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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	Not Yet Assigned		
		Filing Date			
		First Named Inventor	Leonard Forbes		
		Group Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
Sheet	2	of	2	Attorney Docket Number	M4065.0381/P381

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JmJ	A	S. Tiwari, et al., "Straddle Gate Transistors: High I_{on}/I_{off} Transistors at Short Gate Lengths" IBM Research Division.	
JmJ	B	W. Long, et al., "Dual-Material Gate (DMG) Field Effect Transistor."	
JmJ	C	N. R. Rueger, et al. "Selective Etching of SiO ₂ Over Polycrystalline Silicon Using CHF ₃ in an Inductively Coupled Plasma Reactor."	
JmJ	D	S. Vallon, et al., "Polysilicon-germanium Gate Patterning Studies in a High Density Plasma Helicon Source", J. Vac. Sci. Technol. A 15(4), Jul/Aug 1997.	
JmJ	E	P. Patel, et al., "Low Temperature VUV Enhanced Growth of Thin Silicon Dioxide Films" Applied Surface Science 46 (1990) 352-356.	
JmJ	F	W. Shindo, et al., "Low-Temperature Large-Grain Poly-Si Direct Deposition by Microwave Plasma Enhanced Chemical Vapor Deposition Using SiH ₄ /Xe", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
JmJ	G	R. Nozawa, et al., "Low Temperature Polycrystalline Silicon Film Formation With and Without Charged Species in an Electron Cyclotron Resonance SiH ₄ /H ₂ Plasma-Enhanced Chemical Vapor Deposition", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
JmJ	H	C. Saha, et al., "Ion Assisted Growth and Characterization of Polycrystalline Silicon and Silicon-Germanium Films" (visited Nov. 18, 1999) < http://www.dialogselect.com/tech/cgi/pres >.	
	I	D. Landheer, et al., "Formation of High Quality Silicon Dioxide Films by Electron-Cyclotron Resonance Plasma Oxidation and Plasma-Enhanced Chemical Vapour Deposition" (visited Oct. 21, 1999) <http://www.dialogselect.com/tech/cgi/pres>.	
	J	K. Usami, et al., "Thin Si Oxide Films for MIS Tunnel Emitter by Hollow Cathode-Enhanced Plasma Oxidation" (visited Oct. 21, 1999) <http://www.dialogselect.com/tech/cgi/pres>.	
	K	K.C. Saraswat, et al. "A Low Temperature Polycrystalline SiGe CMOS TFT Technology for Large Area AMOLED Drivers" (visited 11/18/99) <http://www.dialogselect.com/tech/cgi/pres>.	

Examiner Signature	T. M. Thomas	Date Considered	06/08/05
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